

제23회 한국반도체학술대회

2016년 2월 22일(월)-24일(수), 강원도 하이원리조트

G. Device & Process Modeling, Simulation and Reliability 분과

Room D

합백Ⅱ+Ⅲ(5층)

2016년 2월 23일(화) 08:30-10:30

[TD1-G] Device Physics and Characterization 1 : Field-Effect Transistors, Thin-Film Transistors, and 3D Inverter

좌장 : 박문수(삼성디스플레이), 이성현(한국외국어대학교)

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| TD1-G-1 | 08:30-08:45 | Analysis of Root Cause of Subthreshold Hump for 40 nm Mobile DDI High-Voltage MOSFET
Kwang-Deok Kim, Sun-Ho Oh, Min-Ki Na, Sung-Gon Choi, Sung-Bo Hwang, and In-Wook Cho
<i>System IC Platform Technology Development team, SK hynix Inc.</i> |
| TD1-G-2 | 08:45-09:00 | Investigation on Effects of Al-Doping in AlZnO Thin Film Transistors using TCAD Simulation
Youngjae Cho ¹ , Young-Min Kong ² , Eomji Kim ³ , Sung-Min Yoon ³ , and Yongwoo Kwon ¹
¹ <i>Department of Materials Science and Engineering, Hongik University,</i>
² <i>School of Materials Science and Engineering, University of Ulsan,</i>
³ <i>Department of Advanced Materials Engineering for Information and Electronics, Kyung Hee University</i> |
| TD1-G-3 | 09:00-09:15 | Low-frequency Noise Behaviors in Dual-gate a-IGZO TFTs
Chan-Yong Jeong ¹ , Jong In Kim ² , Jong-Ho Lee ² , Jae-Gwang Um ³ , Jin Jang ³ , and Hyuck-In Kwon ¹
¹ <i>School of Electrical and Electronics Engineering, Chung-Ang University,</i> ² <i>School of Electrical Engineering and Computer Science, Seoul National University,</i> ³ <i>Department of Information Display, Advanced Display Research Center, Kyung Hee University</i> |
| TD1-G-4 | 09:15-09:30 | Improved Split C-V Technique for Accurate Extraction of Mobility by Considering Effective Inversion Charges in p-Channel Si_{0.8}Ge_{0.2} MOSFET
Tewook Bang ¹ , Hagyoul Bae ¹ , Choong-Ki Kim ¹ , Jae Hur ¹ , Jun-Young Park ¹ , Dae-Chul Ahn ¹ , Gun-Hee Kim ¹ , Yun-Ik Son ² , Jae-Hoon Lee ² , Yong-Taik Kim ² , and Yang-Kyu Choi ¹
¹ <i>School of Electrical Engineering, KAIST,</i> ² <i>SK hynix Inc.</i> |
| TD1-G-5 | 09:30-09:45 | Separate Extraction of Source and Drain Resistances using Double Sweep Saturation Current-Voltage Characteristic in SiGe pMOSFETs
Gun-Hee Kim, Hagyoul Bae, Yong-Yoon Kim, Choong-Ki Kim, Te-Wook Bang, Yoon-Ik Son, and Yang-Kyu Choi
¹ <i>School of Electrical Engineering, KAIST,</i> ² <i>SK hynix Inc.</i> |

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- TD1-G-6** **09:45-10:00** **A New Method for Determination of Subgap Density of States in n/p-type LTPS TFTs**
Injae Lee¹, Miryeon Kim¹, Min-Ho Shin², and Hyungsoon Shin¹
¹*Department of Electronics Engineering, Ewha Womans University,*
²*R&D Center Paju LCD Industrial Complex*
- TD1-G-7** **10:00-10:15** **5 nm 세대 나노 와이어의 기생 커패시턴스 성분 분석 및 추출**
김종수, 서영수, 김현수, 신형철
Inter-university Semiconductor Research Center and School of Electrical Engineering and Computer Science, Seoul National University
- TD1-G-8** **10:15-10:30** **SPICE Parameter Extraction in 3D Sequential Inverter**
Tae Jun Ahn¹ and YunSeop Yu²
¹*Department of Electronic Engineering, Hankyong National University,*
²*Department of Electrical, Electronic and Control Engineering, Hankyong National University*